

L7	11	(fet or (field adj effect adj transistor)) and wafer and ((lattice adj constant) and (epitaxy or epitaxial or epitaxially) and ((tensile adj strain) near10 (direction or perpendicular or parallel)) and gate and (source or drain or source/drain))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 06:01
L8	0	(fet or (field adj effect adj transistor)) and wafer and ((lattice adj constant) near10 (direction or perpendicular or parallel)) and (epitaxy or epitaxial or epitaxially) and ((tensile adj strain) near10 (direction or perpendicular or parallel)) and gate and (source or drain or source/drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 06:01
L9	0	(fet or (field adj effect adj transistor)) and wafer and ((lattice adj constant) near10 (direction or perpendicular or parallel)) and (epitaxy or epitaxial or epitaxially) and ((tensile adj strain) near10 (direction or perpendicular or parallel)) and gate and (source or drain or source/drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 06:01
L10	5	(fet or (field adj effect adj transistor)) and ((lattice adj constant) near10 (direction or perpendicular or parallel)) and (epitaxy or epitaxial or epitaxially) and ((tensile adj strain) near10 (direction or perpendicular or parallel)) and gate and (source or drain or source/drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 06:02
L11	0	((fet or (field adj effect adj transistor)) and ((lattice adj constant) near10 (direction or perpendicular or parallel)) and (epitaxy or epitaxial or epitaxially) and ((tensile adj strain) near10 (direction or perpendicular or parallel)) and gate and (source or drain or source/drain)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 06:02
L12	0	((fet or (field adj effect adj transistor)) and ((lattice adj constant) near10 (direction or perpendicular or parallel)) and (epitaxy or epitaxial or epitaxially) and ((tensile adj strain) near10 (direction or perpendicular or parallel)) and gate and (source or drain or source/drain)).ti;ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 06:02

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	467	(fet or (field adj effect adj transistor)) and wafer and (lattice adj constant) and (epitaxy or epitaxial or epitaxially) and (strain) and gate and (source or drain or source/drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 05:57
L2	117	(fet or (field adj effect adj transistor)) and wafer and (lattice adj constant) and (epitaxy or epitaxial or epitaxially) and (tensile adj strain) and gate and (source or drain or source/drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 05:57
L3	10	(fet or (field adj effect adj transistor)) and wafer and (lattice adj constant) and (epitaxy or epitaxial or epitaxially) and ((tensile adj strain) near5 (direction or perpendicular or parallel)) and gate and (source or drain or source/drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 06:00
L4	0	10/710274	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 05:59

L13	2	((fet or (field adj effect adj transistor)) and ((lattice adj constant) near10 (direction or perpendicular or parallel)).ti,ab, clm. and (epitaxy or epitaxial or epitaxially) and ((tensile adj strain) near10 (direction or perpendicular or parallel)) and gate and (source or drain or source/drain))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 06:02
L14	0	((fet or (field adj effect adj transistor)) and ((lattice adj constant) near10 (direction or perpendicular or parallel)).ti,ab, clm. and (epitaxy or epitaxial or epitaxially) and ((tensile adj strain) near10 (direction or perpendicular or parallel))).ti,ab, clm. and gate and (source or drain or source/drain))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 06:03
L15	1	((fet or (field adj effect adj transistor)) and ((lattice adj constant) near10 (direction or perpendicular or parallel)).ti,ab, clm. and (epitaxy or epitaxial or epitaxially) and ((strain) near10 (direction or perpendicular or parallel)).ti,ab,clm. and gate and (source or drain or source/drain))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 06:03